

FEATURES

- Near Infrared Reduced Footprint Photodiode
- Photosensitive active area: 0.6mm x 0.6mm
- High Sensitivity: 0.65 A/W ($\lambda=850\text{nm}$)
- Wide Operating Temperature: -40°C TO +110°C
- Ideal for High Volume Laser Monitoring Applications
- RoHS and REACH Compliant

Dimensions are in inch [metric] units

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

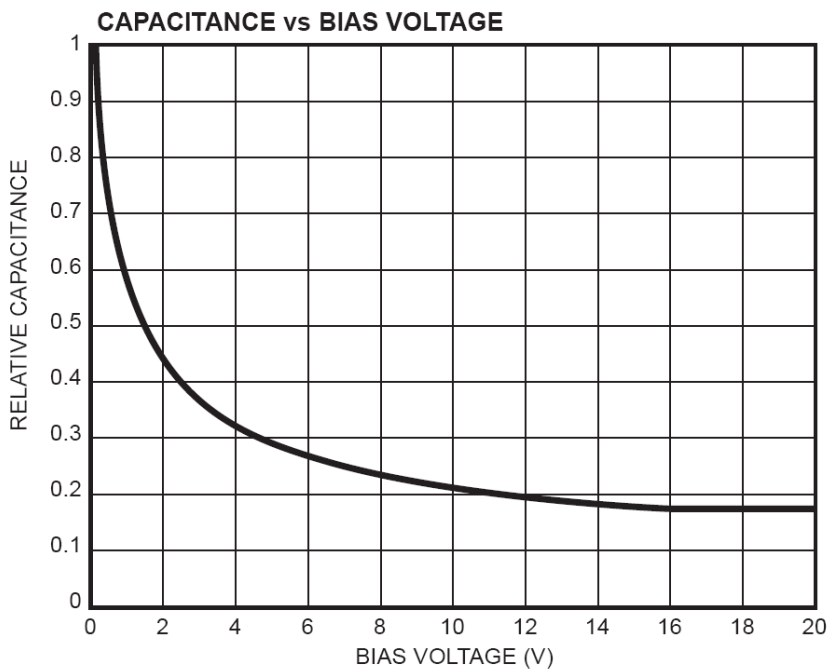
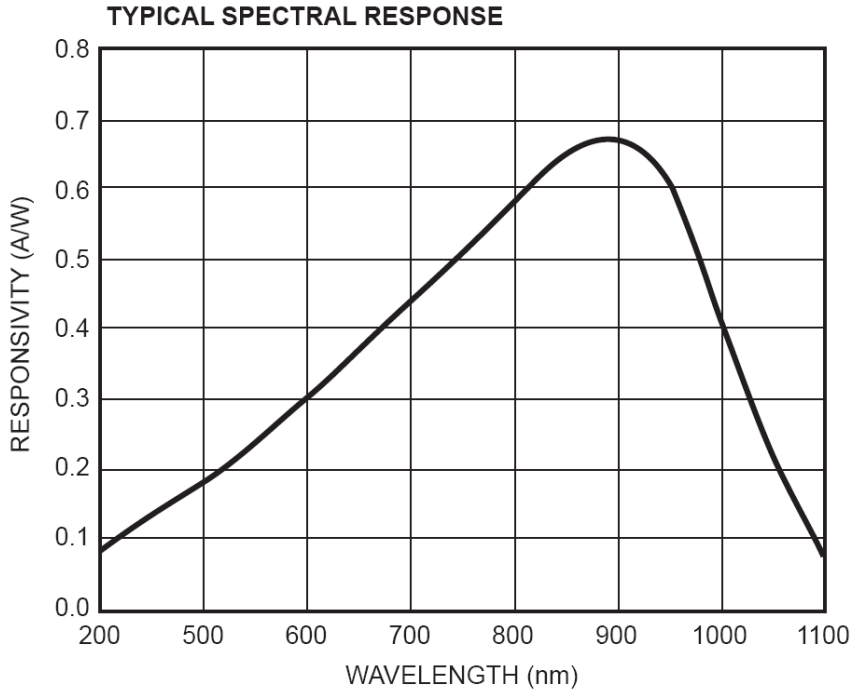
PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Active Area			.36		mm ²
Responsivity, \mathcal{R}	@ 850nm		.65		A/W
Dark Current, I_{dr}	$V_r = 3V$		0.05	0.3	nA
Shunt Resistance	$V_R = 10mV$	200	1000		M Ω
Reverse Breakdown Voltage, V_R	$I_R = 10\mu A$	25			Volts
Capacitance, C	$V_R = 0V$			8	pF
Rise Time	$V_R = 10V$		8	15	nsec

THERMAL PARAMETERS

Storage and Operating Temperature Range	-40°C TO 110°C
Maximum Junction Temperature	110°C



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ORDERING INFORMATION

ODD-850-004-1 Waffle Pack
ODD-850-004-2 Grip Ring



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